

INTEGRATED CIRCUIT STRUCTURE WITH ELECTRICAL STRAP

ABSTRACT

A method of forming an IC is presented. The method includes providing a substrate having a plurality of transistors formed thereon. The transistors have gate stack, source and drain regions. An electrical strap is formed and in contact with at least a portion of at least one sidewall of the gate stack of a first transistor to provide a continuous electrical flowpath over a gate electrode of the first transistor and the source or drain region of a second transistor.

Figure 12